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| APPLICATION NO. | FILING DATE | FIRST NAMED INVENTOR | ATTORNEY DOCKET NO. | CONFIRMATION NO. |
|-----------------|-------------------------------------|----------------------|---------------------|------------------|
| 09/961,291 | 09/25/2001 | Takeyuki Itabashi | 501.37226VX1 | 6791 |
| 20457 75 | 590 12/17/2004 | | EXAM | INER |
| | , TERRY, STOUT & SEVENTEENTH STR | ORTIZ, EDGARDO | | |
| SUITE 1800 | SE VERVIEEN III OIR | | ART UNIT | PAPER NUMBER |
| ARLINGTON, | VA 22209-9889 | | 2815 | |

DATE MAILED: 12/17/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

| | | | 4)(|
|--|---|---|-------------|
| | Application No. | Applicant(s) | |
| | 09/961,291 | ITABASHI ET AL. | |
| Office Action Summary | Examiner | Art Unit | |
| | Edgardo Ortiz | 2815 | |
| The MAILING DATE of this communication Period for Reply | appears on the cover sheet w | rith the correspondence address | , |
| A SHORTENED STATUTORY PERIOD FOR RE THE MAILING DATE OF THIS COMMUNICATIO - Extensions of time may be available under the provisions of 37 CFF after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a - If NO period for reply is specified above, the maximum statutory per - Failure to reply within the set or extended period for reply will, by state of the period for reply will be stated to the peri | ON. R 1.136(a). In no event, however, may a . I reply within the statutory minimum of thi I riod will apply and will expire SIX (6) MOI atute, cause the application to become A | reply be timely filed rly (30) days will be considered timely. NTHS from the mailing date of this communication in the mailing date of the communication in the mailing date of the communication in the mailing date of the communication in | lion. |
| Status . | | | |
| 1)⊠ Responsive to communication(s) filed on 2: | 2 September 2004. | | |
| | This action is non-final. | | |
| 3) Since this application is in condition for allo | wance except for formal mat | ters, prosecution as to the merits | is |
| closed in accordance with the practice unde | • | • | |
| Disposition of Claims | | | |
| 4) Claim(s) 1-20 is/are pending in the applicat 4a) Of the above claim(s) 8-20 is/are withdres 5) Claim(s) is/are allowed. 6) Claim(s) 1-7 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and | awn from consideration. | | |
| Application Papers | | | |
| 9) The specification is objected to by the Exam | | = | |
| 10) The drawing(s) filed on is/are: a) a | | | |
| Applicant may not request that any objection to | | | 4.4.7 |
| Replacement drawing sheet(s) including the cor 11) The oath or declaration is objected to by the | | | |
| Priority under 35 U.S.C. § 119 | | | |
| 12) Acknowledgment is made of a claim for fore a) All b) Some * c) None of: 1. Certified copies of the priority docum 2. Certified copies of the priority docum 3. Copies of the certified copies of the papplication from the International Bur * See the attached detailed Office action for a | nents have been received. The sents have been received in Appropriate to the sent of the | Application No n received in this National Stage | |
| Attachment(s) | | | |
| 1) Notice of References Cited (PTO-892) | 4) Interview | Summary (PTO-413) | |
| Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB Paper No(s)/Mail Date | | (s)/Mail Date Informal Patent Application (PTO-152) | |

DETAILED ACTION

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Election/Restrictions

1. Applicant's election with traverse of species IV, and the argument that claim 1 is generic to all species, in the reply filed on September 22, 2004 is acknowledged.

Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1-6 are rejected under 35 U.S.C. 102(b) as being anticipated by Krishnan et al. (U.S. Patent No. 5,451,551). With regard to Claim 1, Krishnan discloses a semiconductor device comprising an insulator layer (16) having at least one of a via-hole (22) for forming a via-stud and a trench (22) for forming a wire, wherein said one (34) of the via-stud and the wire is formed directly on inner surfaces of said one of the via-hole and the trench (column 3, lines 42-51), through a barrier layer (24) which is made of a high-melting point metal (Titanium-Tungsten), and wherein said one of the via-stud and the wire is formed of said metal (column 3, lines 35-38; column 4, lines 20-32 and figure 7).

With regard to Claim 2, Krishnan discloses a semiconductor device comprising insulator layers (16) having a via-stud and insulator layers having a wire, said insulator layers having said via-stud and said insulator layers having said wire being alternately formed (figure 2), wherein said

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via-stud and said wire are respectively formed in a via-hole (22) and a trench (22) directly on inner surfaces of said one of the via-hole and the trench (column 3, lines 42-51), respectively, through a barrier layer (24) which is made of a high-melting point metal (Titanium-Tungsten), and wherein said one of the via-stud and the wire is formed of said metal (column 3, lines 35-38; column 4, lines 20-32 and figure 7).

With regard to Claim 3, Krishnan discloses a semiconductor device comprising an insulator layer (16) having at least one of a via-hole (20) for forming a via-stud and a trench (22) for forming a wire, wherein said one of a via-stud and the wire is formed directly on inner surfaces of said one of the via-hole and the trench, through a barrier layer (24) which is made of a high-melting point metal (Titanium-Tungsten), and wherein said one of the via-stud and the wire is formed of said metal (column 3, lines 35-38; column 4, lines 20-32 and figure 7). It is noted that the limitation "through electroplating after electro-less plating of said metal" is a product-by-process limitation. The presence of process limitations on product claims, which product does not otherwise patentably distinguish over prior art, cannot impart patentability to the product. In re-Stephens 145 USPQ 656 (CCPA 1965).

With regard to Clam 4, Krishnan discloses a semiconductor device comprising an insulator layer (16) having at least one of a via-hole (20) for forming a via-stud and a trench (22) for forming a wire, wherein said one of a via-stud and the wire is formed directly on inner surfaces of said one of the via-hole and the trench, through a barrier layer (24) which is made of a high-melting point metal (Titanium-Tungsten), and wherein said one of the via-stud and the wire is formed of said

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metal (column 3, lines 35-38; column 4, lines 20-32 and figure 7). It is noted that the limitation "wherein the whole of said one of via-stud and the wire is formed through electro-less plating" is a product-by-process limitation. The presence of process limitations on product claims, which product does not otherwise patentably distinguish over prior art, cannot impart patentability to the product. In re Stephens 145 USPQ 656 (CCPA 1965).

With regard to Claim 5, Krishnan discloses a semiconductor device comprising insulator layers (16) having a via-stud and insulator layers having a wire, said insulator layers having said viastud and said insulator layers having said wire being alternately formed (figure 2), wherein said via-stud and said wire are respectively formed in a via-hole (22) and a trench (22) directly on inner surfaces of said one of the via-hole and the trench (column 3, lines 42-51), respectively, through a barrier layer (24) which is made of a high-melting point metal (Titanium-Tungsten), and wherein said one of the via-stud and the wire is formed of said metal (column 3, lines 35-38; column 4, lines 20-32 and figure 7). It is noted that the limitation "wherein an entirety of said via-stud and an entirety said wire formed through electro-less plating" is a product-by-process limitation. The presence of process limitations on product claims, which product does not otherwise patentably distinguish over prior art, cannot impart patentability to the product. In re Stephens 145 USPQ 656 (CCPA 1965).

With regard to Claim 6, Krishnan discloses a semiconductor device comprising an insulator layer (16) having at least one of a via-hole (20) for forming a via-stud and a trench (22) for forming a wire, wherein said one of a via-stud and the wire is formed directly on inner surfaces of said one

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of the via-hole and the trench, through a barrier layer (24) which is made of a high-melting point metal (Titanium-Tungsten), and wherein said one of the via-stud and the wire is formed of said metal (column 3, lines 35-38; column 4, lines 20-32 and figure 7). It is noted that the limitation "wherein an entirety of said via-stud and an entirety said wire are formed through electro-less plating" is a product-by-process limitation. The presence of process limitations on product claims, which product does not otherwise patentably distinguish over prior art, cannot impart patentability to the product. In re Stephens 145 USPQ 656 (CCPA 1965).

Claim Rejections - 35 USC § 103

- 3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claim 7 is rejected under 35 U.S.C. 103(a) as being unpatentable over Krishnan et al. (U.S. Patent No. 5,451,551). With regard to Claim 7, Krishnan essentially discloses the claimed invention but fails to disclose, the claimed diameter of the via-stud smaller than 0.3 µm.

However, it would have been obvious to someone with ordinary skill in the art at the time of the invention, to modify the structure as disclosed by Krishnan to include the claimed diameter of the via-stud smaller than $0.3 \mu m$, since it has been held that where the general conditions of a claim are disclosed in the prior art, discovering the optimum or working ranges involves only routine skill in the art. In re Aller, 105 USPQ 233. In the instant case, such a modification in the

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Krishnan structure would result in an optimization in the overall size of the final structure and reduction in process time and use of materials.

Conclusion

4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Edgardo Ortiz whose telephone number is 571-272-1735. The examiner can normally be reached on Monday-Friday (1st Friday Off).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on 571-272-1664. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

E.d.

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